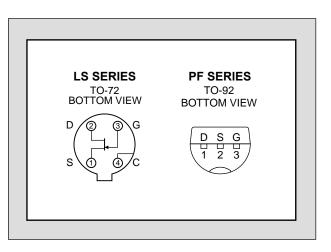
LINEAR SYSTEMS

Linear Integrated Systems

FEATURES					
DIRECT REPLACEMENT FOR LF5301, PF5301, & 2N5301					
HIGH INPUT INPEDANCE	I _G = 0.100 pA				
HIGH GAIN	g _{fs} = 70 μS				
ABSOLUTE MAXIMUM RATINGS ¹					
@ 25 °C (unless otherwise stated)					
Maximum Temperatures					
Storage Temperature (TO-72)	-65 to 175°C				
Storage Temperature (TO-92)	-65 to 150°C				
Maximum Power Dissipation					
Continuous Power Dissipation	300mW				
Maximum Currents					
Gate Current	50mA				
Maximum Voltages					
Gate to Drain	-30V				
Gate to Source	-30V				

LS5301, PF5301

VERY HIGH INPUT IMPEDANCE N-CHANNEL JFET



COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNIT	CONDITIONS
BV _{GSS}	Gate to Source Breakdown Voltage	-30			V	$V_{DS} = 0V, I_D = -1\mu A$
V _{GS(off)}	Gate to Source Cutoff Voltage	0.6		3.0	v	V _{DS} = 10V, I _D = 1nA
I _{GSS}	Gate Leakage Current			-1	n۸	$V_{DS} = 0V, V_{GS} = -15V$
l _G	Gate Operating Current		0.04		pА	V _{DG} = 6V, I _D = 5µA
I _{DSS}	Drain to Source Saturation Current	30		500	μA	V_{DS} = 10V, V_{GS} = 0V
g fs	Forward Transconductance	70		300	μS	V_{DS} = 10V, V_{GS} = 0V, <i>f</i> = 1kHz
C _{iss}	Input Capacitance			3	рF	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$
C _{rss}	Reverse Transfer Capacitance			1.5	рг	$v_{\rm DS} = 10v, v_{\rm GS} = 0v, T = 10012$
en	Equivalent Noise Voltage		45	150	nV/√Hz	V _{DG} = 10V, I _D = 50µA, <i>f</i> = 100Hz

NOTES

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

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